

# Dual Switching Diode Common Cathode

## Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## MAXIMUM RATINGS (EACH DIODE)

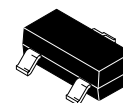
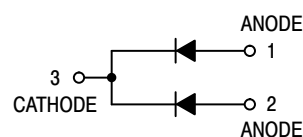
Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	70	V
Forward Current	$I_F$	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA

## THERMAL CHARACTERISTICS

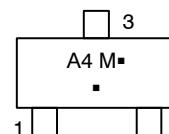
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.


**SOT-23**


## MARKING DIAGRAM



A4= Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## ORDERING INFORMATION

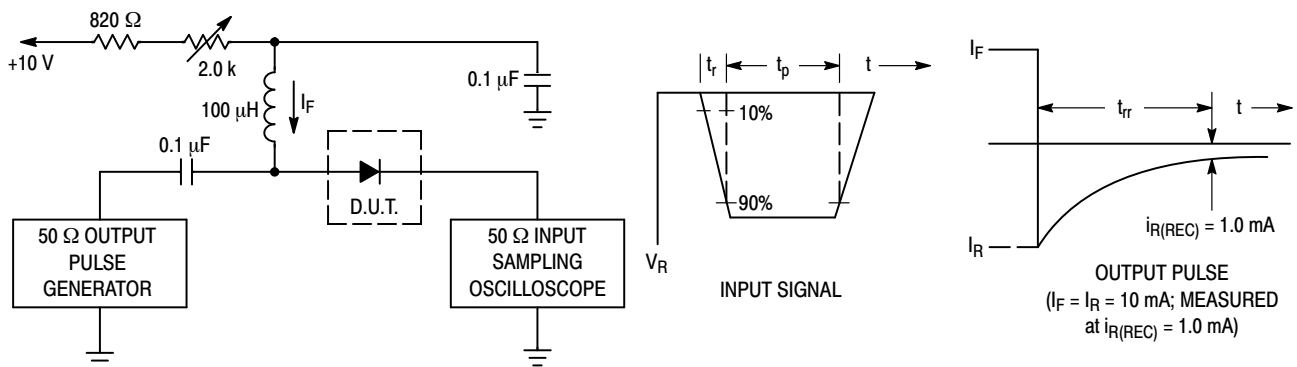
Device	Package	Shipping <sup>†</sup>
BAV70	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ( $I_{(BR)} = 100 \mu\text{A}$ )	$V_{(BR)}$	70	-	V
Reverse Voltage Leakage Current (Note 3) ( $V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$ ) ( $V_R = 70 \text{ V}$ ) ( $V_R = 70 \text{ V}, T_J = 150^\circ\text{C}$ )	$I_R$	-	60 2.5 100	$\mu\text{A}$
Diode Capacitance ( $V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$ )	$C_D$	-	1.5	pF
Forward Voltage ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 10 \text{ mA}$ ) ( $I_F = 50 \text{ mA}$ ) ( $I_F = 150 \text{ mA}$ )	$V_F$	-	715 855 1000 1250	mV
Reverse Recovery Time $R_L = 100 \Omega$ ( $I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA}$ ) (Figure 1)	$t_{rr}$	-	6.0	ns

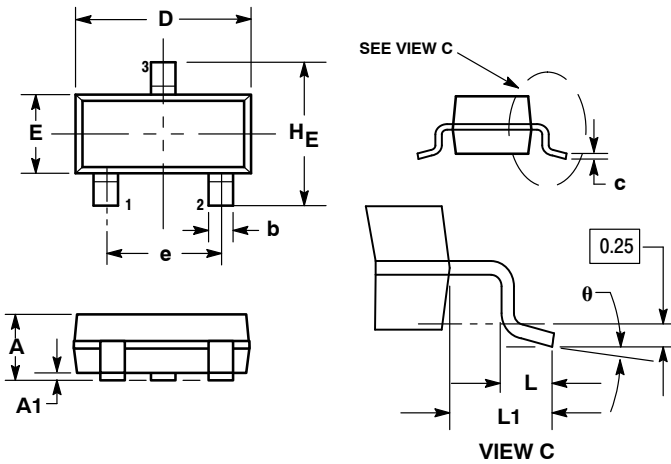
3. For each individual diode while second diode is unbiased.



- Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.
- 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.
- 3.  $t_p > t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

## SOT-23



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

- PIN 1. ANODE  
 2. ANODE  
 3. CATHODE

### SOLDERING FOOTPRINT

